

## Asymmetric GTO Thyristors

- Free-floating silicon
- High-dynamic voltage capability at turn-off
- Low on-state and switching losses
- Coaxial gate leads soldered
- Reverse avalanche capability

## Asymmetrische GTO Thyristoren

- Freier Druckkontakt
- Hohe dynamische Spannungsfestigkeit beim Ausschalten
- Geringe Schaltverluste
- Koaxiales Gate-Kabel angelötet
- Avalanche-Eigenschaften in Sperrichtung

## Thyristors GTO asymétriques

- Contact par pression directe
- Tenue en tension dynamique élevée à l'extinction
- Faible perte de puissance
- Câble de gâchette coaxial soudé
- Caractéristique "avalanche" en sens inverse

T25-20

Ordering number Bestellnummer Num. de commande	V <sub>DRM</sub> V	V <sub>RRM</sub> V <sub>GRRM</sub> V	I <sub>TGQM</sub> A	C <sub>s</sub> μF	I <sub>TAVM</sub> T <sub>c</sub> =85° A	I <sub>TSM</sub> (T <sub>VJM</sub> ) 10 ms kA	V <sub>T</sub> (I <sub>T</sub> = I <sub>TGQM</sub> ) V	I <sub>GT</sub> A	T <sub>VJM</sub> °C	R <sub>thJC</sub> K/W	F kN	Fig. No.	Datasheet Datenblatt Feuille technique
YS 550 101 XX P14...P24	1400...2400	18	700	1	305	5	2.5	0.8	125	0.05	7	33	YSG 701
YS 570 102 XX P14...P24	1400...2400	18	1000	2	550	10	2.3	1.5	125	0.03	16	34	YSG 1000
YS 570 101 XX P14...P24	1400...2400	18	1500	3	550	10	2.5	1.5	125	0.03	16	34	YSG 1500
YS 580 102 XX P14...P24	1400...2400	18	2000	4	1040	16	2.5	3	125	0.015	22	35	YSG 2000
YS 580 104 XX P14...P24	1400...2400	18	2000	4	1040	16	2.5	3	125	0.015	22	36	YSG 2001
YS 580 101 XX P14...P24	1400...2400	18	2500	6	1040	17	2.7	3	125	0.015	33	35	YSG 2500
YS 580 103 XX P14...P24	1400...2400	18	2500	6	1040	17	2.7	3	125	0.015	33	36	YSG 2501
CSG 601-25A01	2500	18	600	1	300	3	3	0.8	125	0.04	11	37	CH-4UH 90006E
CSG 2001-25A01	2500	17	2000	4	830	16	2.8	2.5	125	0.017	22	38	CH-4UH 90005E
CSG 2501-25A01	2500	17	2500	6	830	16	3.1	2.5	125	0.017	22	38	CH-4UH 90009E
CSG 603-45A01	4500	17	600	1	170	2.5	4.5	1.5	125	0.05	11	39	CH-4UH 90010E
CSG 2003-45A01	4500	17	2000	4	640	13	3.5	2.5	125	0.02	22	38	CH-4UH 90011E
CSG 3003-45A01	4500	17	3000	6	790	24	4	4	125	0.015	40	40	CH-4UH 90008E

## Reverse Conducting GTO Thyristors

- Monolithic integration of GTO and freewheeling diode
- Small size and less weight
- Low on-state and switching losses
- Coaxial gate leads
- less induction losses

## Rückwärtsleitende GTO Thyristoren

- GTO-Thyristor und Freilaufdiode auf einer Siliziumtablette
- Platz- und Gewichtsersparnis
- Geringe Schaltverluste
- Koaxiales Gate-Kabel
- Geringe Induktionsverluste

## Thyristors GTO à conduction inverse

- Intégration monolithique d'un thyristor GTO et d'une diode à roue libre
- Economie de place et de poids
- Faible pert de puissance
- Câble de gâchette coaxial
- Faible perte d'induction

Type Ordering number Bestellnummer Num. de commande	V <sub>DRM</sub> V	V <sub>GRM</sub> V	I <sub>TGQM</sub> A	C <sub>s</sub> μF	I <sub>TAVM</sub> T <sub>c</sub> =85° A	I <sub>TSM</sub> (T <sub>VJM</sub> ) 10 ms kA	V <sub>T</sub> (I <sub>T</sub> = I <sub>TGQM</sub> ) V	I <sub>GT</sub> A	T <sub>VJM</sub> °C	R <sub>thJC</sub> K/W	F kN	Fig. No.	Datasheet Datenblatt Feuille technique
CRG 2001-25A01	2500	17	2000	3	700	14	3.5	2.5	125	0.017	40	40	
CRG 2003-45A01	4500	17	2000	4	520	11	4.4	2.5	125	0.02	40	40	

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**Dimensions in mm**

A = Anode  
K = Cathode  
G = Gate  
HK = Auxiliary cathode

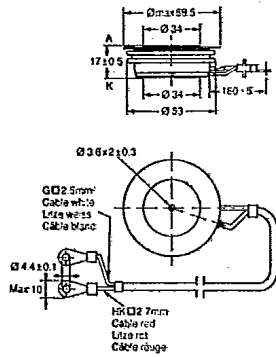
**Abmessungen in mm**

A = Anode  
K = Kathode  
G = Gate  
HK = Hilfskathode

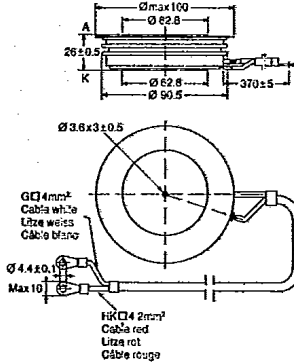
**Dimensions en mm**

A = Anode  
K = Cathode  
G = Gâchette  
HK = Cathode auxiliaire

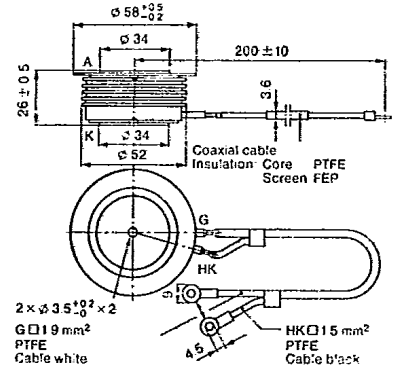
**Fig. 33**



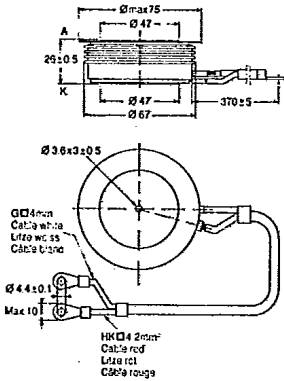
**Fig. 36**



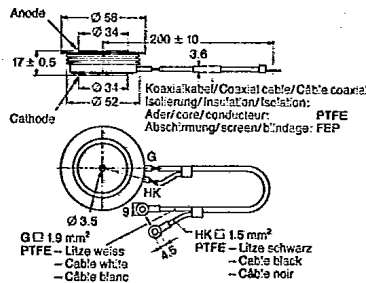
**Fig. 39**



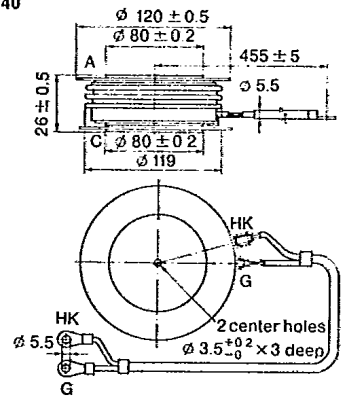
**Fig. 34**



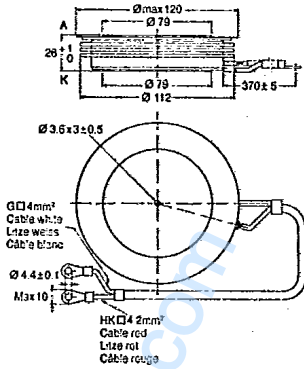
**Fig. 37**



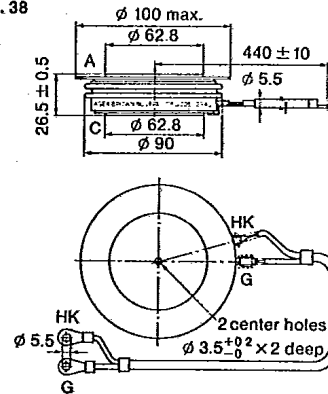
**Fig. 40**



**Fig. 35**



**Fig. 38**



**Fig. 41**

Active part of a reverse conducting GTO thyristor with the diode at the rim.

Aktiv-Teil eines rückwärtsleitenden GTO-Thyristors mit Diode am Rand.

Partie actif d'une GTO thyristor à conduction inverse avec diode incorporé.

